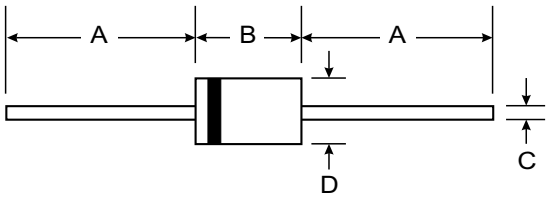
1N914/A/B

75mA Axial Leaded High Speed Switching Diodes

Features

- High switching speed: max. 4 ns
- Continuous reverse voltage:max. 75 V
- Repetitive peak reverse voltage:max. 100 V
- Repetitive peak forward current: max. 225 mA



Mechanical Data

- **Case:** DO-35 Glass Case
- **Weight:** approx. 0.13g

DO-35		
Dim	**Min**	**Max**
A	25.40	—
B	—	4.00
C	—	0.60
D	—	2.00
All Dimensions in mm		

Maximum Ratings and Electrical Characteristics @ T_A = 25°C unless otherwise specified

Parameter	Symbol	Value	Unit
Maximum Repetitive Peak Reverse Voltage	V_{RRM}	100	V
Maximum Continuous Reverse Voltage	V_{RM}	75	V
Maximum Continuous Forward Current	I_F	75	mA
Maximum Power Dissipation	P_D	250	mW
Maximum Repetitive Peak Forward Current	I_{FRM}	225	mA
Maximum Non-repetitive Peak Forward Current at t = 1s	I_{FSM}	0.5	A
Maximum Junction Temperature	T_J	175	°C
Storage Temperature Range	T_S	-65 to + 200	°C

Parameter		Symbol	Test Condition	Min	Typ	Max	Unit
Reverse Current		I_R	V_R = 20 V	-	-	25	nA
			V_R = 20 V , Tj = 150 °C	-	-	50	μA
Forward Voltage	**1N914**	V_F	I_F = 10 mA	-	-	1.0	V
	1N914A		I_F = 20 mA	-	-	1.0	V
	1N914B		I_F = 5 mA	0.62	-	0.72	V
	1N914B		I_F = 100 mA	-	-	1.0	V
Diode Capacitance		Cd	f = 1MHz ; V_R = 0	-	-	4.0	pF
Reverse Recovery Time		Trr	I_F = 10 mA to I_R = 60 mA R_L = 100 Ω ; measured at I_R = 1mA	-	-	4	ns

FIG. 1 MAXIMUM PERMISSIBLE CONTINUOUS FORWARD CURRENT AS A FUNCTION OF AMBIENT TEMPERATURE.

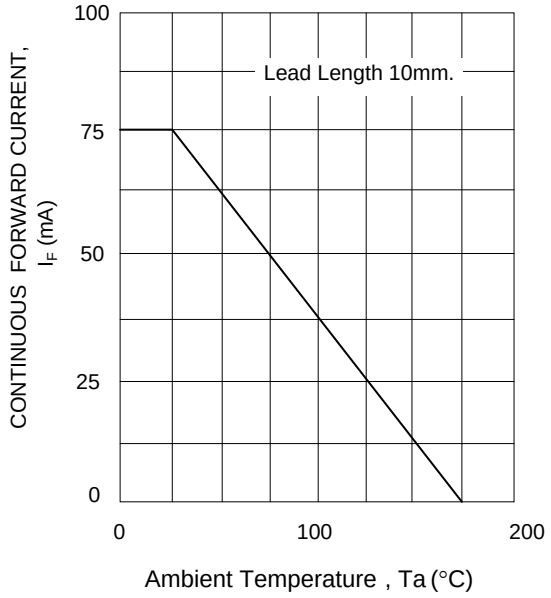


FIG. 2 TYPICAL FORWARD VOLTAGE

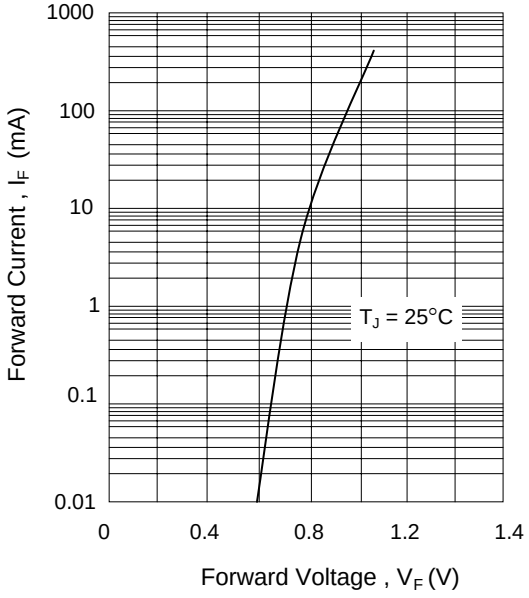


FIG. 3 TYPICAL DIODE CAPACITANCE AS A FUNCTION OF REVERSE VOLTAGE

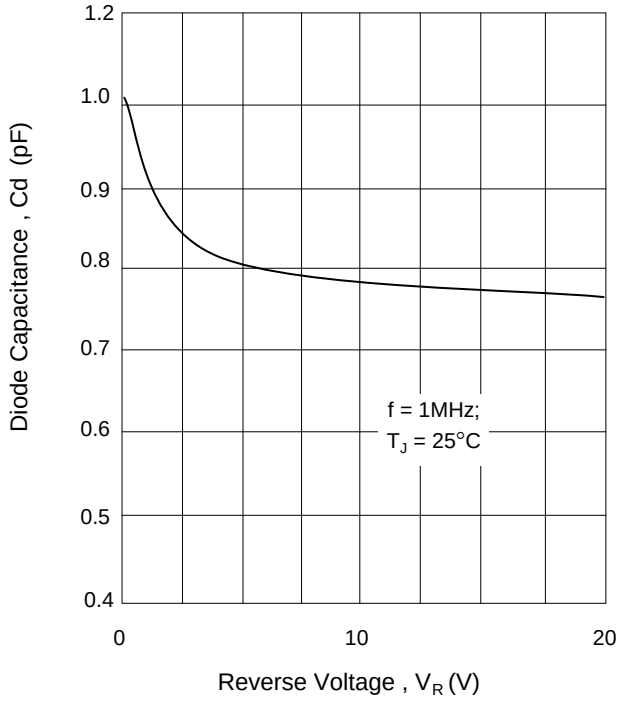


FIG. 4 TYPICAL REVERESE CURRENT VERSUS JUNCTION TEMPERATURE